
1SS110

Silicon Epitaxial Planar Diode for Tuner Band Switch

HITACHI

ADE-208-179B (Z)
Rev. 2

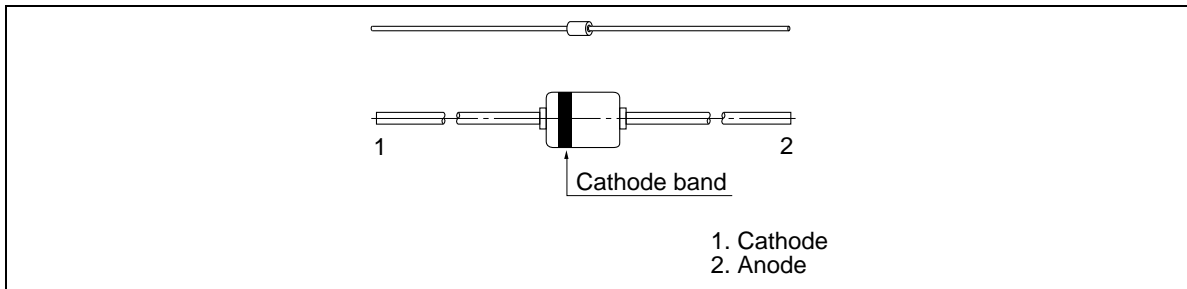
Features

- Low forward resistance. ($r_f = 0.9\Omega_{\max}$)
- Suitable for 5mm pitch high speed automatic insertion.
- Small glass package (MHD) enables easy mounting and high reliability.

Ordering Information

| Type No. | Cathode band | Package Code |
|----------|--------------|--------------|
| 1SS110 | Verdure | MHD |

Outline



1SS110

Absolute Maximum Ratings (Ta = 25°C)

| Item | Symbol | Value | Unit |
|----------------------|-----------|-------------|------|
| Reverse voltage | V_R | 35 | V |
| Forward current | I_F | 100 | mA |
| Junction temperature | T_j | 175 | °C |
| Storage temperature | T_{stg} | -65 to +175 | °C |

Electrical Characteristics (Ta = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test Condition |
|--------------------|--------|-----|-----|-----|---------------|--|
| Forward voltage | V_F | — | — | 1.0 | V | $I_F = 10\text{mA}$ |
| Reverse voltage | V_R | 35 | — | — | V | $I_R = 10\mu\text{A}$ |
| Reverse current | I_R | — | — | 0.1 | μA | $V_R = 25\text{V}$ |
| Capacitance | C | — | — | 1.2 | pF | $V_R = 6\text{V}$, $f = 1\text{MHz}$ |
| Forward resistance | r_f | — | — | 0.9 | Ω | $I_F = 2\text{mA}$, $f = 100\text{MHz}$ |

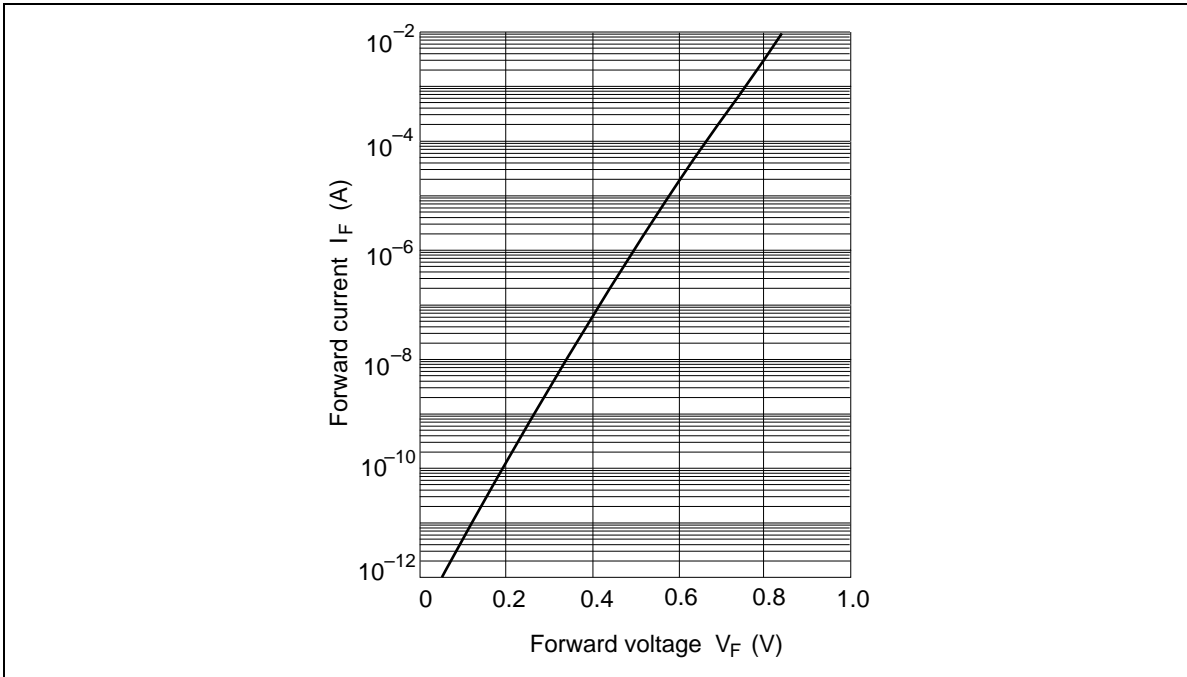


Fig.1 Forward current Vs. Forward voltage

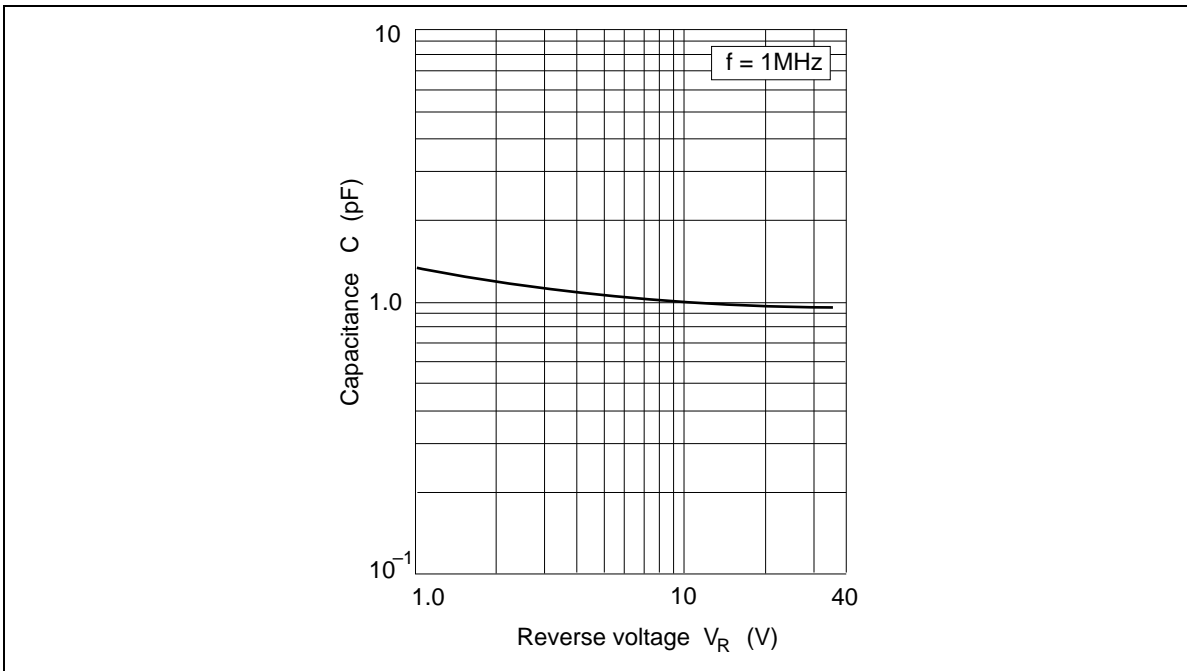


Fig.2 Capacitance Vs. Reverse voltage

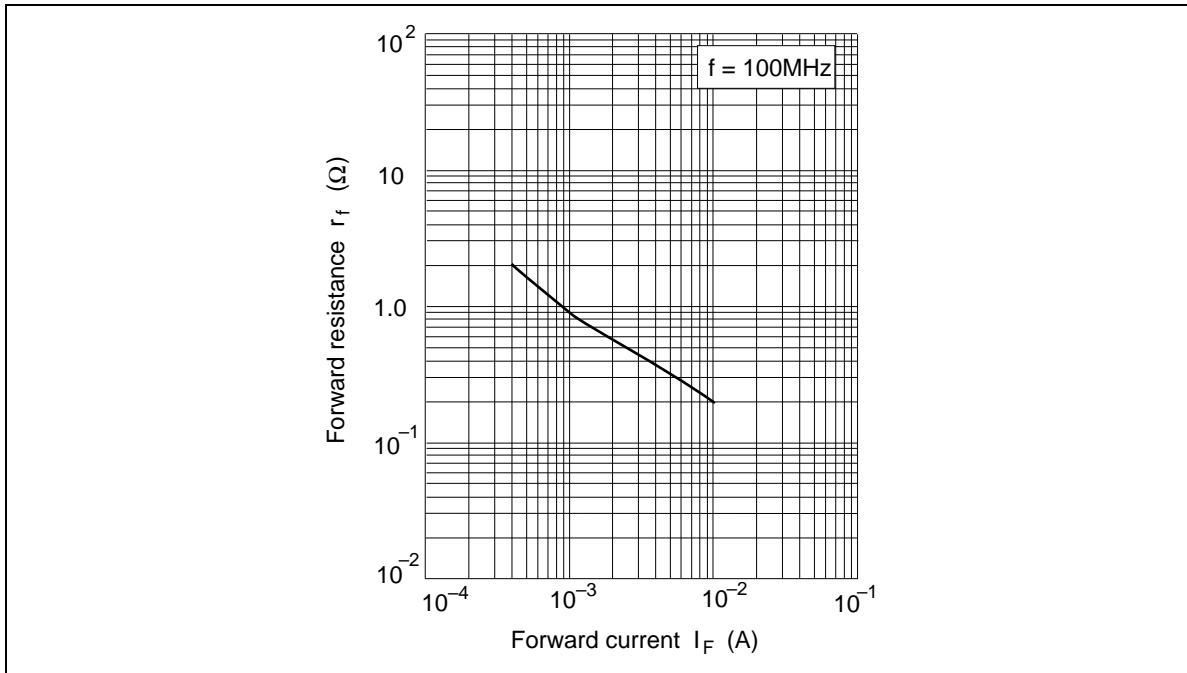
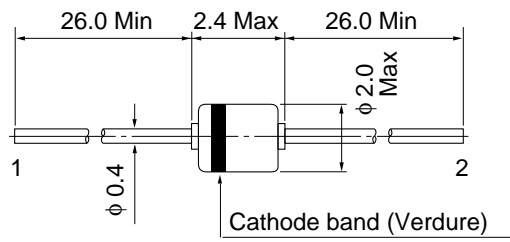


Fig.3 Forward resistance Vs. Forward current

Package Dimensions

Unit: mm



- 1 Cathode
- 2 Anode

| | |
|--------------|-------|
| HITACHI Code | MHD |
| JEDEC Code | DO-34 |
| EIAJ Code | — |
| Weight (g) | 0.084 |